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(54) **Title:** A HETEROEPI TAXIAL WAFER FOR THE DEPOSITION OF GALLIUM NITRIDE

(57) **Abstract:** A heteroepitaxial wafer comprising in the following order (1) a substrate made of Silicon having a thickness a diameter and a resistivity, comprising a buried gettering layer for Hydrogen, (2) a 3C-SiC layer, (3) an Aluminum-Nitride nucleation layer, comprising in the given order a first nitrogen enriched Aluminum-Nitride region, an Aluminum-Nitride region and a second nitrogen enriched Aluminum-Nitride region.



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